

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	5501	("memory cell" or "memory area" or "memory portion") and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	4852	@ad<=20000525 and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	4534	substrate and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	4381	semiconductor and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L8	2359	(peripheral or logic) and 4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB